



GaAs SPDT RF Switch DC - 3 GHz

SW-219 V3

Features

Fast Switching Speed: 6 nS TypicalUltra Low DC Power Consumption

• Small Package Size: 0.180" (4.6 mm) Sq.

Description

M/A-COM's SW-219 is a GaAs MMIC SPDT switch packaged in a surface mount CR-3 or a CR-10 ceramic style package. The SW-219 is a low loss, high isolation SPDT that has broadband application from DC to 3 GHz. The CR-3 and CR-10 packages are hermetically sealed, making these switches ideal for space, military radios, or other environmentally harsh applications.

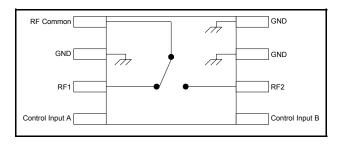
Typical applications include synthesizer switching, transmit/receive switching, switch matrices and filter banks in systems such as radio and cellular equipment, PCM, GPS, and fiber optic modules.

The SW-219 is fabricated as a monolithic GaAs MMIC using a 1.0 micron MESFET process.

Ordering Information

Part Number	Package		
SW-219	Ceramic (CR-3)		
SW-219G	Ceramic with Gull Wing (CR-10)		
SW-219B	Screened to MIL-STD-883C, Method 5008.4, Table VII, Class B Hybrid		

Functional Schematic ¹



1. Bottom of case is AC Ground.

Pin Configuration

Pin No.	Function	Pin No.	Function	
1	RF Common	5	Control Input B	
2	Ground	6	RF Port 2	
3	RF Port 1	7	Ground	
4	Control Input A	8	Ground	

Absolute Maximum Ratings ^{2,3}

Parameter	Absolute Maximum
Input Power 0.05 GHz 0.5 - 2.0 GHz	+27 dBm +34 dBm
Control Voltage	-8.5 V <u><</u> Vc <u><</u> +5 V
Operating Temperature	-55°C to +125°C
Storage Temperature	-65°C to +150°C

- 2. Exceeding any one or combination of these limits may cause permanent damage to this device.
- M/A-COM does not recommend sustained operation near these survivability limits.

[•] Europe Tel: 44.1908.574.200 / Fax: 44.1908.574.300

Asia/Pacific Tel: 81.44.844.8296 / Fax: 81.44.844.8298





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Electrical Specifications: $T_A = -55$ to +85°C, $V_C = 0$ V / -5 V, $Z_0 = 50$ Ω

Parameter	Test Conditions Ur		Min	Тур	Max
Insertion Loss	DC - 0.5 GHz		_ _ _	0.7 0.8 0.8 0.9	
Isolation	DC - 0.5 GHz		38 28	_ _ _	
VSWR	DC - 0.5 GHz DC - 1 GHz DC - 2 GHz DC - 3 GHz	DC - 1 GHz Ratio — DC - 2 GHz Ratio —		_ _ _	1.2:1 1.2:1 1.3:1 1.6:1
Trise, Tfall	10% to 90% RF, 90% to 10% RF nS -		_	3	_
Ton, Toff	50% control to 90% RF, 50% control to 10% RF nS		_	6	_
Transients	In-Band mV		_	10	_
Input P1dB	0.5 - 3 GHz, 0 / -5 VDC		_ _ _	27 21 33 26	_ _ _
IP2	For two-tone input power up to +13 dBm 0.5 - 3 GHz dBm — 0.05 GHz dBm —		_	62 68	_
IP3	For two-tone input power up to +13 dBm 0.5 - 3 GHz dBm 0.05 GHz dBm		_	40 46	
Control Current	Vc = 0 to 0.2 V		_ _ _	50 —	20 — 300

^{4.} See MIL-STD-883 for environmental screening options.

Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

Truth Table 5,6

Control Input		Condition of Switch, RF Common to each RF Por	
Α	В	RF1	RF2
1	0	On	Off
0	1	Off	On

^{5.} 0 = 0 V to -0.2 V, 1 = -5 V to -8 V

^{6.} When an RF output is off, it is shorted to ground.

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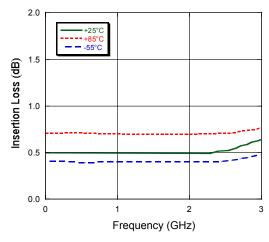


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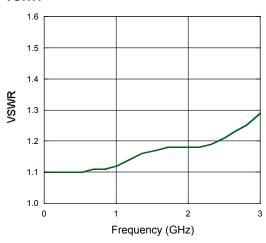
SW-219 V3

Typical Performance Curves

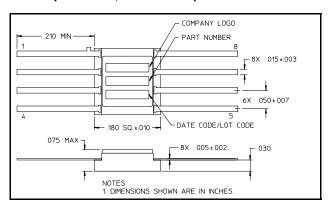
Insertion Loss



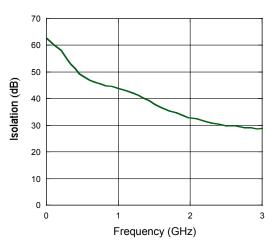
VSWR



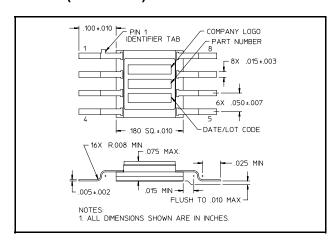
CR-3 (SW-219, SW-219B)



Isolation



CR-10 (SW-219G)



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